



60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE IntelliFET MOSFET

Product Summary

Continuous Drain Source Voltage
 On-state Resistance
 Nominal Load Current (V_{IN} = 5V)
 Clamping Energy
 60V
 200mΩ
 2.0A
 490mJ

Description

The ZXMS6005DGQ-13 is a self protected low side IntelliFETTM MOSFET with logic level input. It integrates over-temperature, over-current, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6005DGQ-13 is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

- Lamp Driver
- Motor Driver
- Relay Driver
- Solenoid Driver

Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Over-current Protection
- Input Protection (ESD)
- High Continuous Current Rating
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

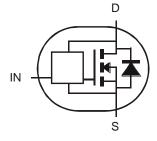
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish ©3
- Weight: 0.12 grams (Approximate)

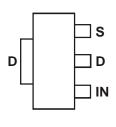




Top View



Device Symbol



Top View Pin Out

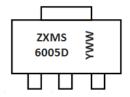
Ordering Information (Note 5)

Ī	Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
	ZXMS6005DGQ-13	ZXMS6005D	13	12	2,500 Units

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

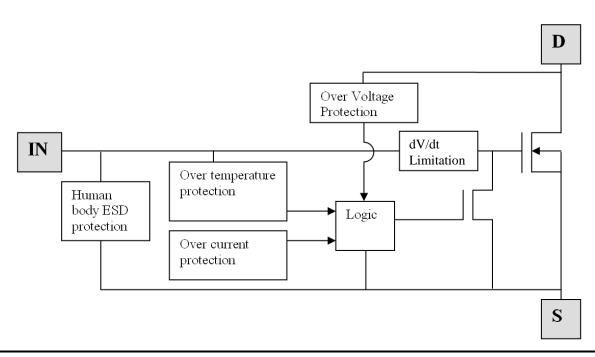
Marking Information



ZXMS6005D = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 8 = 2018) WW or \overline{WW} = Week Code (01 to 53)



Functional Block Diagram



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V_{DS}	60	V
Drain-Source Voltage for Short Circuit Protection	V _{DS(SC)}	24	V
Continuous Input Voltage	V _{IN}	-0.5 to +6	V
Continuous Input Current @-0.2V \leq V _{IN} \leq 6V Continuous Input Current @V _{IN} $<$ -0.2V or V _{IN} $>$ 6V	I _{IN}	No limit I _{IN} ≤2	mA
Pulsed Drain Current @V _{IN} = 3.3V	I _{DM}	5	Α
Pulsed Drain Current @V _{IN} = 5V	I _{DM}	6	Α
Continuous Source Current (Body Diode) (Note 6)	Is	2.5	Α
Pulsed Source Current (Body Diode)	I _{SM}	10	А
Unclamped Single Pulse Inductive Energy, T _J = +25°C, I _D = 0.5A, V _{DD} = 24V	E _{AS}	490	mJ
Electrostatic Discharge (Human Body Model)	V _{ESD}	4000	V
Charged Device Model	V _{CDM}	1000	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C (Note 6) Linear Derating Factor	P _D	1.32 10.5	W mW/°C
Power Dissipation at T _A = +25°C (Note 7) Linear Derating Factor	P _D	1.69 13.5	W mW/°C
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	94.8	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	74	°C/W
Thermal Resistance, Junction to Case (Note 8)	R _{eJC}	9.3	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 8. Thermal resistance between junction and the mounting surfaces of drain and source pins.

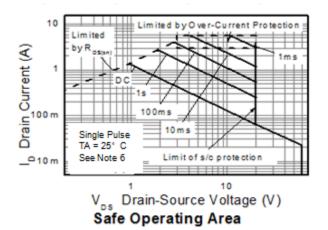


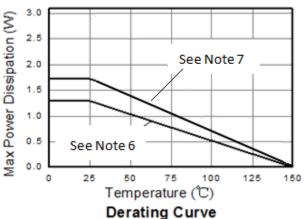
Recommended Operating Conditions

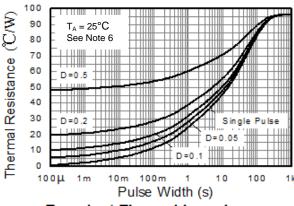
The ZXMS6005DGQ-13 is optimized for use with μC operating from 3.3V and 5V supplies.

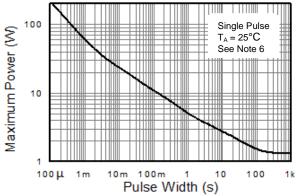
Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V _{IN}	0	5.5	V
Ambient Temperature Range	T _A	-40	+125	°C
High Level Input Voltage for MOSFET to be on	V _{IH}	3	5.5	V
Low Level Input Voltage for MOSFET to be off	V _{IL}	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	V _P	0	24	V

Thermal Characteristics









Transient Thermal Impedance

Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

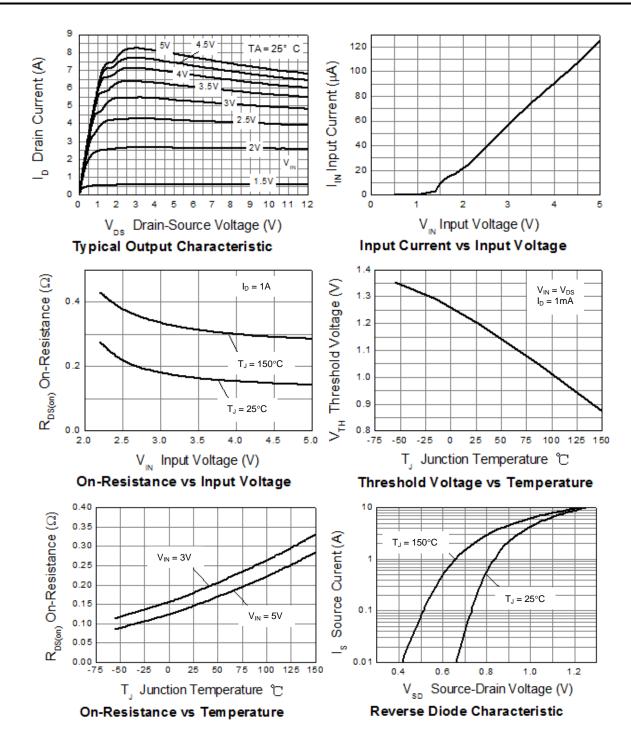
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	V _{DS(AZ)}	60	65	70	V	$I_D = 10mA$
Off State Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 12V, V_{IN} = 0V$
On State Drain Current		_	_	2		$V_{DS} = 36V, V_{IN} = 0V$
Input Threshold Voltage	V _{IN(TH)}	0.7	1.2	1.5	V	$V_{DS} = V_{GS}$, $I_D = 1mA$
Input Current	_	_	60	100	μΑ	$V_{IN} = 3V$
Input Current	I _{IN}	_	120	200		$V_{IN} = 5V$
Input Current While Over Temperature Active	_	_	_	300	μΑ	V _{IN} = 5V
Static Drain-Source On-State Resistance	7	_	170	250	mΩ	$V_{IN} = 3V, I_D = 1A$
Static Drain-Source On-State Resistance	R _{DS(ON)}	_	150	200		$V_{IN} = 5V, I_D = 1A$
Continuous Proin Current (Note 6)	- I _D	1.4	_	_	A	$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 6)		1.6	_	_		$V_{IN} = 5V, T_A = +25^{\circ}C$
Continuous Prais Current (Note 7)		1.9	_	_		$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 7)		2.0	_	_		$V_{IN} = 5V, T_A = +25^{\circ}C$
Current Limit (Note 0)	I _{D(LIM)}	2.2	5	_	Α	$V_{IN} = 3V$
Current Limit (Note 9)		3.3	7	_		$V_{IN} = 5V$
Dynamic Characteristics						
Turn On Delay Time	t _{D(ON)}	_	6	_		Vpp = 12V. lp = 1A. Vgs = 5V
Rise Time	t _R	_	14	_		
Turn Off Delay Time	t _{D(OFF)}	_	34	_	μs	$V_{DD} = 12V$, $I_D = 1A$, $V_{GS} = 5V$
Fall Time	t _F	_	19	_		
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 10)	T _{JT}	+150	+175	_	°C	_
Thermal Hysteresis (Note 10)	f _f	_	+10	_	°C	_

Notes:

- The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.
- 10. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

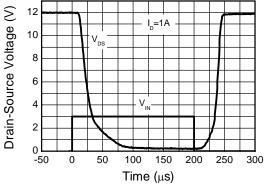


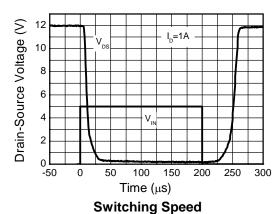
Typical Characteristics





Typical Characteristics (Cont.)





Switching Speed

 $V_{IN} = 5V$ V_{DS} = 15V Drain Current (A) $R_{_D} = 0\Omega$ __ 4 6 10 Time (ms)

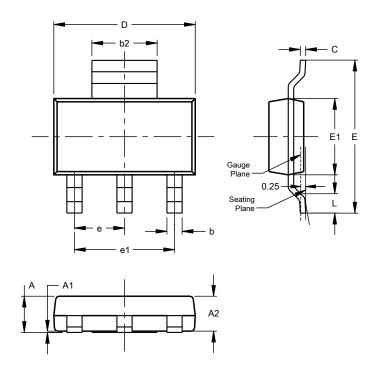
Typical Short Circuit Protection



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

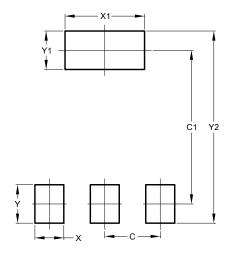


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A 1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70	-		
Е	6.70	7.30			
E1	3.30	3.70			
е	е		2.30		
e1			4.60		
L	0.85				
All [All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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